

Andrew J Steckl

List of Publications by Year in descending order

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23500

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93
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360
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360
docs citations

360
times ranked

9005
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced emission efficiency in organic light-emitting diodes using deoxyribonucleic acid complex as an electron blocking layer. Applied Physics Letters, 2006, 88, 1711-1719.	1.5	301
2	DNA "a new material for photonics?". Nature Photonics, 2007, 1, 3-5.	15.6	297
3	Superhydrophobic and Oleophobic Fibers by Coaxial Electrospinning. Langmuir, 2009, 25, 9454-9462.	1.6	293
4	Red light emission by photoluminescence and electroluminescence from Eu-doped GaN. Applied Physics Letters, 1999, 75, 1189-1191.	1.5	267
5	Optoelectronic Properties and Applications of Rare-Earth-Doped GaN. MRS Bulletin, 1999, 24, 33-38.	1.7	266
6	A nearly ideal phosphor-converted white light-emitting diode. Applied Physics Letters, 2008, 92, .	1.5	264
7	Rare-earth-doped GaN: growth, properties, and fabrication of electroluminescent devices. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 749-766.	1.9	262
8	Visible emission from Er-doped GaN grown by solid source molecular beam epitaxy. Applied Physics Letters, 1998, 73, 1700-1702.	1.5	208
9	High-voltage Ni- and Pt-SiC Schottky diodes utilizing metal field plate termination. IEEE Transactions on Electron Devices, 1999, 46, 456-464.	1.6	187
10	Triaxial Electrospun Nanofiber Membranes for Controlled Dual Release of Functional Molecules. ACS Applied Materials & Interfaces, 2013, 5, 8241-8245.	4.0	185
11	Coaxial Electrospinning Formation of Complex Polymer Fibers and their Applications. ChemPlusChem, 2019, 84, 1453-1497.	1.3	182
12	Aptamer-based lateral flow assay for point of care cortisol detection in sweat. Sensors and Actuators B: Chemical, 2019, 283, 79-86.	4.0	176
13	Stress Biomarkers in Biological Fluids and Their Point-of-Use Detection. ACS Sensors, 2018, 3, 2025-2044.	4.0	175
14	Blue emission from Tm-doped GaN electroluminescent devices. Applied Physics Letters, 1999, 75, 2184-2186.	1.5	152
15	Photocatalytic Self Cleaning Textile Fibers by Coaxial Electrospinning. ACS Applied Materials & Interfaces, 2010, 2, 2448-2455.	4.0	138
16	Red light emission by photoluminescence and electroluminescence from Pr-doped GaN on Si substrates. Applied Physics Letters, 1999, 74, 2161-2163.	1.5	130
17	Spectral and time-resolved photoluminescence studies of Eu-doped GaN. Applied Physics Letters, 2003, 82, 1655-1657.	1.5	130
18	Electrowetting on Paper for Electronic Paper Display. ACS Applied Materials & Interfaces, 2010, 2, 3318-3323.	4.0	130

#	ARTICLE	IF	CITATIONS
19	A Review of SiC Reactive Ion Etching in Fluorinated Plasmas. <i>Physica Status Solidi (B): Basic Research</i> , 1997, 202, 605-642.	0.7	127
20	Epitaxial growth of beta -SiC on Si by RTCVD with C/sub 3/H/sub 8/ and SiH/sub 4/. <i>IEEE Transactions on Electron Devices</i> , 1992, 39, 64-74.	1.6	122
21	Nucleation and Void Formation Mechanisms in SiC Thin Film Growth on Si by Carbonization. <i>Journal of the Electrochemical Society</i> , 1995, 142, 634-641.	1.3	118
22	Long-term antimicrobial effect of nisin released from electrospun triaxial fiber membranes. <i>Acta Biomaterialia</i> , 2017, 53, 242-249.	4.1	114
23	Three-color electrowetting display device for electronic paper. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	112
24	Refractory metal silicides: Thin-film properties and processing technology. <i>IEEE Transactions on Electron Devices</i> , 1983, 30, 1480-1497.	1.6	111
25	Photoluminescence and lasing from deoxyribonucleic acid (DNA) thin films doped with sulforhodamine. <i>Applied Optics</i> , 2007, 46, 1507.	2.1	109
26	Paper Microfluidics for Point-of-Care Blood-Based Analysis and Diagnostics. <i>Analytical Chemistry</i> , 2019, 91, 352-371.	3.2	109
27	Three-color integration on rare-earth-doped GaN electroluminescent thin films. <i>Applied Physics Letters</i> , 2003, 82, 502-504.	1.5	107
28	Laser action in Eu-doped GaN thin-film cavity at room temperature. <i>Applied Physics Letters</i> , 2004, 85, 4588-4590.	1.5	103
29	Blood coagulation screening using a paper-based microfluidic lateral flow device. <i>Lab on A Chip</i> , 2014, 14, 4035-4041.	3.1	101
30	Green electroluminescence from Er-doped GaN Schottky barrier diodes. <i>Applied Physics Letters</i> , 1998, 73, 2450-2452.	1.5	90
31	Prospects for rare earth doped GaN lasers on Si. <i>Materials Today</i> , 2007, 10, 20-27.	8.3	90
32	Reactive ion etching of SiC thin films using fluorinated gases. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986, 4, 349.	1.6	88
33	Reactive Ion Etching of SiC Thin Films by Mixtures of Fluorinated Gases and Oxygen. <i>Journal of the Electrochemical Society</i> , 1990, 137, 212-220.	1.3	87
34	Multiple color capability from rare earth-doped gallium nitride. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001, 81, 97-101.	1.7	87
35	Visible and infrared rare-earth-activated electroluminescence from indium tin oxide Schottky diodes to GaN:Er on Si. <i>Applied Physics Letters</i> , 1999, 74, 182-184.	1.5	84
36	Aptamer-Based Lateral Flow Biosensor for Rapid Detection of Salivary Cortisol. <i>ACS Omega</i> , 2020, 5, 32890-32898.	1.6	83

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37	Exploring the Potential of Nucleic Acid Bases in Organic Light Emitting Diodes. <i>Advanced Materials</i> , 2015, 27, 7552-7562.	11.1	82
38	Structural characterization of nanometer SiC films grown on Si. <i>Applied Physics Letters</i> , 1993, 62, 3135-3137.	1.5	78
39	Photoluminescence studies of rare earth (Er, Eu, Tm) in situ doped GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003, 105, 91-96.	1.7	78
40	Optical and magnetic properties of Eu-doped GaN. <i>Applied Physics Letters</i> , 2006, 89, 132119.	1.5	77
41	Growth of crystalline 3C-SiC on Si at reduced temperatures by chemical vapor deposition from silacyclobutane. <i>Applied Physics Letters</i> , 1993, 63, 3347-3349.	1.5	76
42	Voltage-controlled yellow or orange emission from GaN codoped with Er and Eu. <i>Applied Physics Letters</i> , 2000, 76, 1525-1527.	1.5	74
43	Lateral flow assay using aptamer-based sensing for on-site detection of dopamine in urine. <i>Analytical Biochemistry</i> , 2020, 596, 113637.	1.1	74
44	Nanofiber-Based Bulk Heterojunction Organic Solar Cells Using Coaxial Electrospinning. <i>Advanced Energy Materials</i> , 2012, 2, 1136-1144.	10.2	70
45	Electrospun Carbon Nanofiber Modified Electrodes for Stripping Voltammetry. <i>Analytical Chemistry</i> , 2015, 87, 9315-9321.	3.2	70
46	Heteroepitaxial Growth of SiC on Si(100) and (111) by Chemical Vapor Deposition Using Trimethylsilane. <i>Journal of the Electrochemical Society</i> , 1999, 146, 1197-1202.	1.3	67
47	Red emission from Eu-doped GaN luminescent films grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2003, 83, 9-11.	1.5	65
48	Demonstration of a visible laser on silicon using Eu-doped GaN thin films. <i>Journal of Applied Physics</i> , 2005, 98, 056108.	1.1	64
49	Improved Performance of OLEDs on Cellulose/Epoxy Substrate Using Adenine as a Hole Injection Layer. <i>ACS Photonics</i> , 2015, 2, 439-445.	3.2	64
50	SiC rapid thermal carbonization of the (111)Si semiconductor-insulator structure and subsequent metalorganic chemical vapor deposition of GaN. <i>Applied Physics Letters</i> , 1996, 69, 2264-2266.	1.5	63
51	High-transmission electrowetting light valves. <i>Applied Physics Letters</i> , 2005, 86, 151121.	1.5	63
52	Green emission from Er-doped GaN grown by molecular beam epitaxy on Si substrates. <i>Applied Physics Letters</i> , 1998, 73, 2143-2145.	1.5	62
53	High speed nanofluidic protein accumulator. <i>Lab on A Chip</i> , 2009, 9, 1890.	3.1	62
54	Label-Free Optical Detection of Multiple Biomarkers in Sweat, Plasma, Urine, and Saliva. <i>ACS Sensors</i> , 2019, 4, 1346-1357.	4.0	62

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55	Maximizing Alq_3 OLED Internal and External Efficiencies: Charge Balanced Device Structure and Color Conversion Outcoupling Lenses. Journal of Display Technology, 2006, 2, 143-152.	1.3	61
56	Circuits on cellulose. IEEE Spectrum, 2013, 50, 48-61.	0.5	61
57	ELiXIR-Solid-State Luminaire With Enhanced Light Extraction by Internal Reflection. Journal of Display Technology, 2007, 3, 155-159.	1.3	60
58	The trials of wafer-scale integration: Although major technical problems have been overcome since WSI was first tried in the 1960s, commercial companies can't yet make it fly. IEEE Spectrum, 1984, 21, 32-39.	0.5	59
59	A comparative study of electrode effects on the electrical and luminescent characteristics of Alq_3 /TPD OLED: Improvements due to conductive polymer (PEDOT) anode. Journal of Luminescence, 2007, 126, 225-229.	1.5	59
60	High brightness phosphorescent organic light emitting diodes on transparent and flexible cellulose films. Nanotechnology, 2014, 25, 094012.	1.3	59
61	The effect of ambient atmosphere in the annealing of indium tin oxide films. Journal of Applied Physics, 1980, 51, 3890-3895.	1.1	57
62	Residue-free reactive ion etching of SiC in CHF_3/O_2 with H_2 additive. Applied Physics Letters, 1992, 60, 1966-1968.	1.5	57
63	Photoluminescence properties of in situ Tm-doped $\text{AlxGa}_{1-x}\text{N}$. Applied Physics Letters, 2003, 83, 4556-4558.	1.5	56
64	Excitation pathways and efficiency of Eu^{2+} ions in GaN by site-selective spectroscopy. Applied Physics B: Lasers and Optics, 2009, 97, 607-618.	1.1	56
65	Stimuli-Responsive Self-Immolative Polymer Nanofiber Membranes Formed by Coaxial Electrospinning. ACS Applied Materials & Interfaces, 2017, 9, 11858-11865.	4.0	55
66	Local structure and bonding of Er in GaN: A contrast with Er in Si. Applied Physics Letters, 2000, 76, 2865-2867.	1.5	54
67	Enhanced blue emission from Tm-doped $\text{AlxGa}_{1-x}\text{N}$ electroluminescent thin films. Applied Physics Letters, 2003, 83, 2094-2096.	1.5	54
68	Temperature dependence of energy transfer mechanisms in Eu-doped GaN. Journal of Applied Physics, 2004, 95, 7717-7724.	1.1	54
69	Voltage Control of Droplet Interface Bilayer Lipid Membrane Dimensions. Langmuir, 2011, 27, 618-626.	1.6	54
70	Residue-free Reactive Ion Etching of Silicon Carbide in Fluorinated Plasmas: II .. Journal of the Electrochemical Society, 1995, 142, 312-319.	1.3	52
71	Localized fabrication of Si nanostructures by focused ion beam implantation. Applied Physics Letters, 1992, 60, 1833-1835.	1.5	50
72	Application of charge-coupled devices to infrared detection and imaging. Proceedings of the IEEE, 1975, 63, 67-74.	16.4	49

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73	Characterization of 3C-SiC crystals grown by thermal decomposition of methyltrichlorosilane. Applied Physics Letters, 1996, 69, 3824-3826.	1.5	49
74	Effects of Hydrogen Additive on Obtaining Residue-Free Reactive Ion Etching of SiC in Fluorinated Plasmas. Journal of the Electrochemical Society, 1993, 140, 1813-1824.	1.3	48
75	Spectroscopic and energy transfer studies of Eu ³⁺ centers in GaN. Journal of Applied Physics, 2007, 102, 073520.	1.1	48
76	Pentacene organic thin-film transistors on flexible paper and glass substrates. Nanotechnology, 2014, 25, 094005.	1.3	48
77	Deactivating Chemical Agents Using Enzyme-Coated Nanofibers Formed by Electrospinning. ACS Applied Materials & Interfaces, 2011, 3, 4633-4639.	4.0	45
78	Effect of carbonization on the growth of 3C-SiC on Si (111) by silacyclobutane. Applied Physics Letters, 1994, 64, 3000-3002.	1.5	44
79	Molecular beam epitaxy growth of SiC on Si(111) from silacyclobutane. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1305.	1.6	44
80	Molecular Beam Deposition of DNA Nanometer Films. Nano Letters, 2007, 7, 133-137.	4.5	43
81	Enhanced blue and green emission in rare-earth-doped GaN electroluminescent devices by optical photopumping. Applied Physics Letters, 2002, 81, 2331-2333.	1.5	42
82	Selective pH-Responsive Core-Shell Nanofiber Membranes for Chem/Bio/Med Applications: Targeted Delivery of Functional Molecules. ACS Applied Materials & Interfaces, 2017, 9, 42653-42660.	4.0	42
83	Doping-induced selective area photoluminescence in porous silicon. Applied Physics Letters, 1993, 62, 1982-1984.	1.5	41
84	Focused ion beam micromilling of GaN and related substrate materials (sapphire, SiC, and Si). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 362.	1.6	41
85	Intense switchable fluorescence in light wave coupled electrowetting devices. Applied Physics Letters, 2005, 86, 011105.	1.5	41
86	Heat conduction in silicon thin films: Effect of microstructure. Journal of Materials Research, 1995, 10, 1889-1896.	1.2	39
87	DNA Bases Thymine and Adenine in Bio-Organic Light Emitting Diodes. Scientific Reports, 2014, 4, 7105.	1.6	39
88	Photoluminescence from stain-etched polycrystalline Si thin films. Applied Physics Letters, 1993, 62, 2111-2113.	1.5	38
89	Optimum Er concentration for in situ doped GaN visible and infrared luminescence. Applied Physics Letters, 2001, 79, 719-721.	1.5	38
90	Optically active centers in Eu implanted, Eu in situ doped GaN, and Eu doped GaN quantum dots. Journal of Applied Physics, 2009, 105, 043104.	1.1	38

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91	Role of Surfactants in the Interaction of Dye Molecules in Natural DNA Polymers. Langmuir, 2009, 25, 11698-11702.	1.6	38
92	Multi-layered core-sheath fiber membranes for controlled drug release in the local treatment of brain tumor. Scientific Reports, 2019, 9, 17936.	1.6	38
93	Thermal Oxidation of Sputtered Silicon Carbide Thin Films. Journal of the Electrochemical Society, 1984, 131, 1907-1914.	1.3	37
94	Photonic Applications of Rare-Earth-Doped Materials. MRS Bulletin, 1999, 24, 16-20.	1.7	37
95	Room-temperature visible and infrared photoluminescence from Pr-implanted GaN films by focused-ion-beam direct write. Applied Physics Letters, 1999, 74, 2364-2366.	1.5	37
96	Effect of optical excitation energy on the red luminescence of Eu ³⁺ in GaN. Applied Physics Letters, 2005, 86, 051110.	1.5	37
97	Microbial Power-Generating Capabilities on Micro-/Nano-Structured Anodes in Micro-Sized Microbial Fuel Cells. Fuel Cells, 2014, 14, 801-809.	1.5	36
98	SiC/Si heterojunction diodes fabricated by self-selective and by blanket rapid thermal chemical vapor deposition. IEEE Transactions on Electron Devices, 1994, 41, 281-287.	1.6	35
99	Silicon Carbide Wafer Bonding. Journal of the Electrochemical Society, 1995, 142, 232-236.	1.3	35
100	Residue-Free Reactive Ion Etching of 3-Å-C and 6-Å-H in Fluorinated Mixture Plasmas. Journal of the Electrochemical Society, 1995, 142, 2853-2860.	1.3	35
101	Triggered Release of Molecules across Droplet Interface Bilayer Lipid Membranes Using Photopolymerizable Lipids. Langmuir, 2012, 28, 7657-7664.	1.6	34
102	Self-inflating floating nanofiber membranes for controlled drug delivery. International Journal of Pharmaceutics, 2020, 579, 119164.	2.6	34
103	Effect of Si codoping on Eu ³⁺ luminescence in GaN. Journal of Applied Physics, 2009, 105, 043107.	1.1	33
104	Plasma Etching of Refractory Gates for VLSI Applications. Journal of the Electrochemical Society, 1984, 131, 2325-2335.	1.3	32
105	Low-voltage GaN:Er green electroluminescent devices. Applied Physics Letters, 2000, 76, 1365-1367.	1.5	32
106	Lateral color integration on rare-earth-doped GaN electroluminescent thin films. Applied Physics Letters, 2002, 80, 1888-1890.	1.5	32
107	Enhanced Performance of Micro-Electro-Mechanical Systems (MEMS) Microbial Fuel Cells Using Electrospun Microfibrous Anode and Optimizing Operation. Fuel Cells, 2013, 13, 336-341.	1.5	32
108	Absorption of Ethylene on Membranes Containing Potassium Permanganate Loaded into Alumina-Nanoparticle-Incorporated Alumina/Carbon Nanofibers. Journal of Agricultural and Food Chemistry, 2018, 66, 5635-5643.	2.4	32

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109	Plasma etching of sputtered Mo and MoSi ₂ thin films in NF ₃ gas mixtures. Journal of Applied Physics, 1982, 53, 5531-5540.	1.1	31
110	Shallow Si-p-n junctions fabricated by focused ion beam Ga-implantation through thin Ti and TiSi ₂ layers. Journal of Applied Physics, 1993, 74, 2318-2322.	1.1	30
111	Integrated OLED as excitation light source in fluorescent lateral flow immunoassays. Biosensors and Bioelectronics, 2015, 74, 150-155.	5.3	30
112	Temperature behavior of visible and infrared electroluminescent devices fabricated on erbium-doped GaN. IEEE Transactions on Electron Devices, 2002, 49, 48-54.	1.6	29
113	Point-of-care coagulation monitoring: first clinical experience using a paper-based lateral flow diagnostic device. Biomedical Microdevices, 2017, 19, 64.	1.4	29
114	Thermal oxidation of niobium silicide thin films. Journal of Applied Physics, 1983, 54, 2716-2719.	1.1	28
115	Damage generation and removal in the Ga ⁺ focused ion beam micromachining of GaN for photonic applications. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 3063.	1.6	28
116	Photoluminescence studies and read/write process of a strong two-photon absorbing chromophore. Applied Physics Letters, 2000, 77, 328-330.	1.5	28
117	SiC thin-film Fabry-Perot interferometer for fiber-optic temperature sensor. IEEE Transactions on Electron Devices, 2003, 50, 2159-2164.	1.6	28
118	In-vitro evaluation of MPA-loaded electrospun coaxial fiber membranes for local treatment of glioblastoma tumor cells. Journal of Drug Delivery Science and Technology, 2017, 40, 45-50.	1.4	27
119	Multilevel interconnections for wafer scale integration. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1986, 4, 3127-3138.	0.9	26
120	Chapter 3 Building Blocks for SiC Devices: Ohmic Contacts, Schottky Contacts, and p-n Junctions. Semiconductors and Semimetals, 1998, 52, 77-160.	0.4	26
121	GaN focused ion beam micromachining with gas-assisted etching. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 2547.	1.6	26
122	Room-temperature-grown rare-earth-doped GaN luminescent thin films. Applied Physics Letters, 2001, 79, 1962-1964.	1.5	26
123	Immunoassay on Free-Standing Electrospun Membranes. ACS Applied Materials & Interfaces, 2010, 2, 252-258.	4.0	26
124	Spectroscopic studies of the visible and infrared luminescence from Er doped GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 116-120.	1.7	25
125	Flow reproducibility of whole blood and other bodily fluids in simplified no reaction lateral flow assay devices. Biomicrofluidics, 2017, 11, 024116.	1.2	25
126	Si Oxyhydrides on Stain-Etched Porous Si Thin Films and Correlation with Crystallinity and Photoluminescence. Journal of the Electrochemical Society, 1995, 142, L69-L71.	1.3	24

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127	Optical amplification and electroluminescence at 1.54 μ m in Er-doped zinc silicate germanate on silicon. Applied Physics Letters, 2004, 84, 1462-1464.	1.5	24
128	Correlation between compositional fluctuation and magnetic properties of Tm-doped AlGaIn alloys. Applied Physics Letters, 2007, 91, 222503.	1.5	24
129	Structural and compositional properties of the PbS ϵ Si heterojunction. Journal of Applied Physics, 1980, 51, 726-737.	1.1	23
130	SiC Silicon ϵ Insulator Structures by Direct Carbonization Conversion and Postgrowth from Silacyclobutane. Journal of the Electrochemical Society, 1994, 141, L66-L68.	1.3	23
131	Stain-etched porous silicon visible light emitting diodes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1221.	1.6	23
132	Versatile Core-Sheath Biofibers using Coaxial Electrospinning. Materials Research Society Symposia Proceedings, 2008, 1094, 1.	0.1	23
133	Effect of growth conditions on Eu ³⁺ luminescence in GaN. Journal of Crystal Growth, 2010, 312, 680-684.	0.7	23
134	Rapid thermal chemical vapor deposition growth of nanometer-thin SiC on silicon. Thin Solid Films, 1992, 216, 149-154.	0.8	22
135	Fabrication of visibly photoluminescent Si microstructures by focused ion beam implantation and wet etching. Applied Physics Letters, 1994, 65, 2081-2083.	1.5	22
136	RBS/Channeling study of Er doped GaN films grown by MBE on Si substrates. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 946-951.	0.6	22
137	Ga flux dependence of Er-doped GaN luminescent thin films. Applied Physics Letters, 2002, 80, 728-730.	1.5	22
138	Site specific Eu ³⁺ stimulated emission in GaN host. Applied Physics Letters, 2006, 88, 011111.	1.5	22
139	Color tunable organic light emitting diodes using Eu complex doping. Solid-State Electronics, 2007, 51, 500-504.	0.8	22
140	Immobilization of Stable Thylakoid Vesicles in Conductive Nanofibers by Electrospinning. Biomacromolecules, 2011, 12, 778-784.	2.6	21
141	Review of focused ion beam implantation mixing for the fabrication of GaAs-based optoelectronic devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2570.	1.6	20
142	GaN:Eu electroluminescent devices grown by interrupted growth epitaxy. Thin Solid Films, 2006, 496, 636-642.	0.8	20
143	Quantitative hematocrit measurement of whole blood in a point-of-care lateral flow device using a smartphone flow tracking app. Biosensors and Bioelectronics, 2020, 163, 112300.	5.3	20
144	Silane silicidation of Mo thin films. Journal of Applied Physics, 1980, 51, 5981-5985.	1.1	19

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145	Growth and morphology of Er-doped GaN on sapphire and hydride vapor phase epitaxy substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1195.	1.6	19
146	Selective enhancement of blue electroluminescence from GaN:Tm. Applied Physics Letters, 2003, 82, 55-57.	1.5	19
147	Photocatalytic cellulosic electrospun fibers for the degradation of potent cyanobacteria toxin microcystin-LR. Journal of Materials Chemistry, 2012, 22, 12666.	6.7	19
148	Plasma etching characteristics of sputtered MoSi ₂ films. Applied Physics Letters, 1980, 37, 466-468.	1.5	18
149	Charge-packet splitting in charge-domain devices. IEEE Transactions on Electron Devices, 1984, 31, 1494-1501.	1.6	18
150	Crystallinity and Photoluminescence in Stain-etched Porous Si. Journal of the Electrochemical Society, 1994, 141, 674-679.	1.3	18
151	Selective compositional mixing in GaAs/AlGaAs superlattice induced by low dose Si focused ion beam implantation. Journal of Applied Physics, 1995, 77, 5616-5624.	1.1	18
152	Growth and characterization of GaN thin films on SiC SOI substrates. Journal of Electronic Materials, 1997, 26, 217-223.	1.0	18
153	In Situ N ₂ -Doping of SiC Films Grown on Si(111) by Chemical Vapor Deposition from Organosilanes. Journal of the Electrochemical Society, 2000, 147, 2324.	1.3	18
154	Excitation-Wavelength Dependent and Time-Resolved Photoluminescence Studies of Europium Doped GaN Grown by Interrupted Growth Epitaxy (IGE). Materials Research Society Symposia Proceedings, 2005, 866, 1.	0.1	18
155	Complementary Electrowetting Devices on Plasma-Treated Fluoropolymer Surfaces. Langmuir, 2010, 26, 9474-9483.	1.6	18
156	Optical channel waveguides in AlGaAs multiple-quantum-well structures formed by focused ion-beam-induced compositional mixing. IEEE Photonics Technology Letters, 1993, 5, 435-438.	1.3	17
157	Highly perfect thin films of SiC: X-ray double crystal diffractometry and X-ray double crystal topographic study. Thin Solid Films, 1997, 292, 1-6.	0.8	17
158	Rare-earth-doped GaN switchable color electroluminescent devices. IEEE Transactions on Electron Devices, 2002, 49, 1545-1551.	1.6	17
159	Light Wave Coupled Flat Panel Displays and Solid-State Lighting Using Hybrid Inorganic/Organic Materials. Journal of Display Technology, 2005, 1, 157-166.	1.3	17
160	Visible electroluminescence from stain-etched porous Si diodes. IEEE Electron Device Letters, 1994, 15, 507-509.	2.2	16
161	Liquid-state field-effect transistors using electrowetting. Applied Physics Letters, 2007, 90, 043507.	1.5	16
162	Electrical and magnetic properties of GaN codoped with Eu and Si. Journal of Applied Physics, 2010, 107, 013901.	1.1	16

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163	Lightweight electrowetting display on ultra-thin glass substrate. Journal of the Society for Information Display, 2013, 21, 192-197.	0.8	16
164	Characterization of NbSi ₂ thin films. Journal of Applied Physics, 1982, 53, 5703-5709.	1.1	15
165	Reduced temperature growth of crystalline 3C-SiC films on 6H-SiC by chemical vapor deposition from silacyclobutane. Journal of Applied Physics, 1995, 78, 1271-1273.	1.1	15
166	Rare earth focused ion beam implantation utilizing Er and Pr liquid alloy ion sources. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2791.	1.6	15
167	Upconversion luminescence of Er-implanted GaN films by focused-ion-beam direct write. Applied Physics Letters, 1999, 75, 1833-1835.	1.5	15
168	High-density Er-implanted GaN optical memory devices. Applied Optics, 2001, 40, 3552.	2.1	15
169	Photoluminescent and electroluminescent Zn ₂ /Si _{0.5} /Ge _{0.5} /O ₄ :Mn thin films for integrated optic devices. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 1420-1426.	1.9	15
170	Versatile electrowetting arrays for smart window applications-from small to large pixels on fixed and flexible substrates. Solar Energy Materials and Solar Cells, 2013, 117, 544-548.	3.0	15
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345	Universal Bacterial Detection Utilizing PEDOT:PSS-Based Organic Electrochemical Transistors. ECS Meeting Abstracts, 2021, MA2021-01, 1416-1416.	0.0	0
346	(Keynote) Blood, Sweat and Tears... â€“ Sensing of Human Performance Biomarkers in Bodily Fluids Using Point-of-Use Devices. ECS Meeting Abstracts, 2021, MA2021-01, 1333-1333.	0.0	0
347	(Electronics and Photonics Division Award) Let There be Light; Research at the Intersection of Electronics and Photonics. ECS Meeting Abstracts, 2022, MA2022-01, 1300-1300.	0.0	0
348	(Invited) Salivary Lipopolysaccharide (LPS) Detection Using Lateral Flow Sandwich-Based Immunoassay Point-of-Care Devices. ECS Meeting Abstracts, 2022, MA2022-01, 2181-2181.	0.0	0